

PSMN1R5-40ES

N-channel 40 V 1.6 m Ω standard level MOSFET in I2PAK.

Rev. 01 — 19 April 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in I2PAK (SOT226) package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	40	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	338	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	[2]	-	1.3	1.6	mΩ
Dynamic ch	Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$		-	32	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 20 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	136	-	nC

^[1] Continuous current is limited by package



^[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		$_{\mathbf{G}}$
mb	D	drain		
				mbb076 Ś
			1 2 3	
			SOT226 (I2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R5-40ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

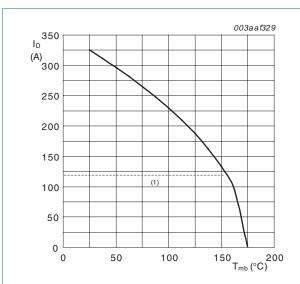
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	40	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}$	[1]	-	120	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 3		-	1301	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	diode					
Is	source current	T _{mb} = 25 °C	[1]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1301	Α
Avalanche ruç	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le$ 40 V; unclamped; R_{GS} = 50 Ω ; t_p = 0.1 ms		-	1.4	J

^[1] Continuous current is limited by package.

PSMN1R5-40ES

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 $V_{\it GS} \geq$ 10 V(1) Capped at 120 A due to package

Fig 1. Normalized continuous drain current as a function of mounting base temperature

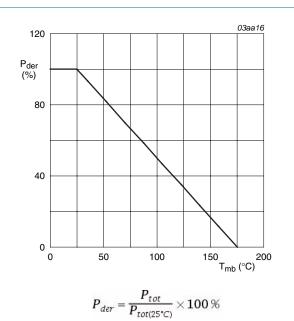
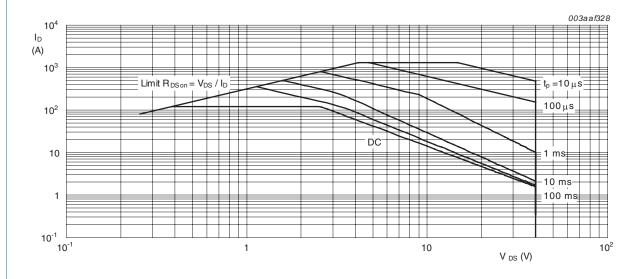


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 T_{mb} = 25 °C; I_{DM} is a single pulse; Capped at 120 A due to package

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

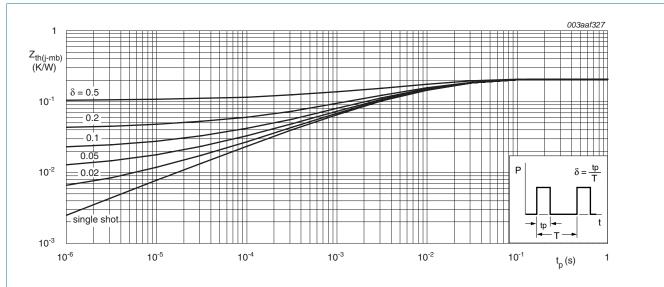


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 11; see Figure 10	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	10	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	250	500	V V V V μA μA nA nA mΩ mΩ mΩ mΩ nC
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	1.9	2.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12	-	2.6	3.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	1] -	1.3	1.6	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	1.1	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 A$; $V_{DS} = 0 V$; $V_{GS} = 10 V$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	133	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	136		nC
Q_{GS}	gate-source charge	see Figure 14; see Figure 15	-	52	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	22	-	nC
Q_{GD}	gate-drain charge		-	32	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 20 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.1	-	V
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9710	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	2042	-	pF
C _{rss}	reverse transfer capacitance		-	994	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 10 \text{ V};$	-	45	-	ns
^t r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	66	-	ns
t _{d(off)}	turn-off delay time		-	111	-	ns
t _f	fall time		-	53	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; \ V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	64	-	ns
Q _r	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; \ V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	117	-	nC

[1] Measured 3 mm from package.

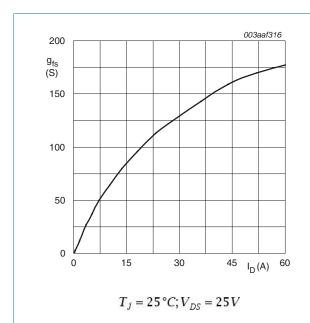


Fig 5. Forward transconductance as a function of drain current; typical values

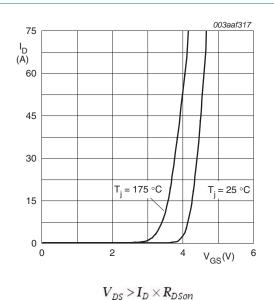


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

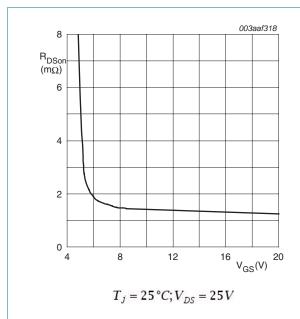


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values.

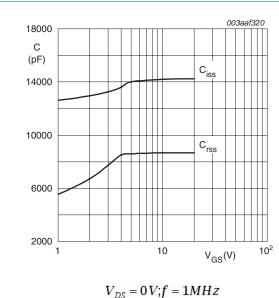


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

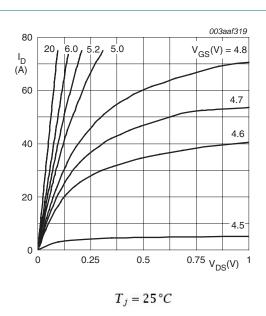


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

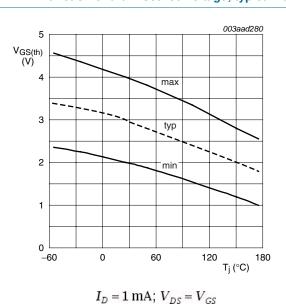


Fig 10. Gate-source threshold voltage as a function of junction temperature

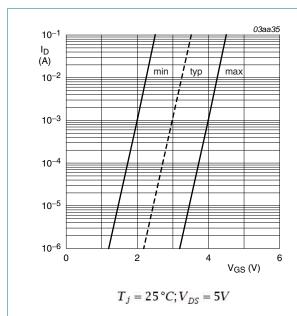


Fig 11. Sub-threshold drain current as a function of gate-source voltage

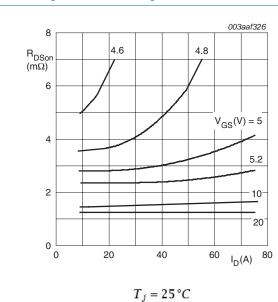


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

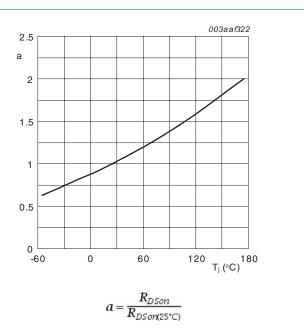


Fig 12. Normalized drain-source on state resistance factor as a function of junction temperature

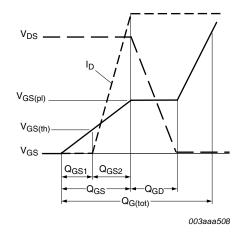


Fig 14. Gate charge waveform definitions

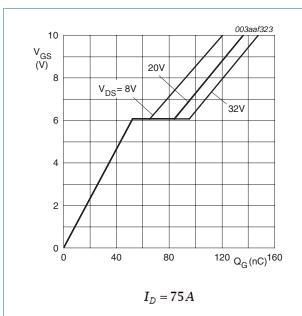
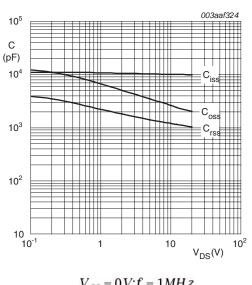


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

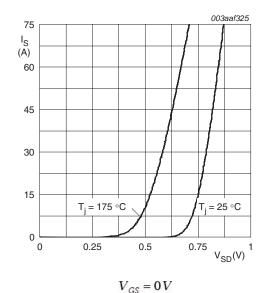


Fig 17. Source current as a function of source-drain voltage; typical values

7. Package outline

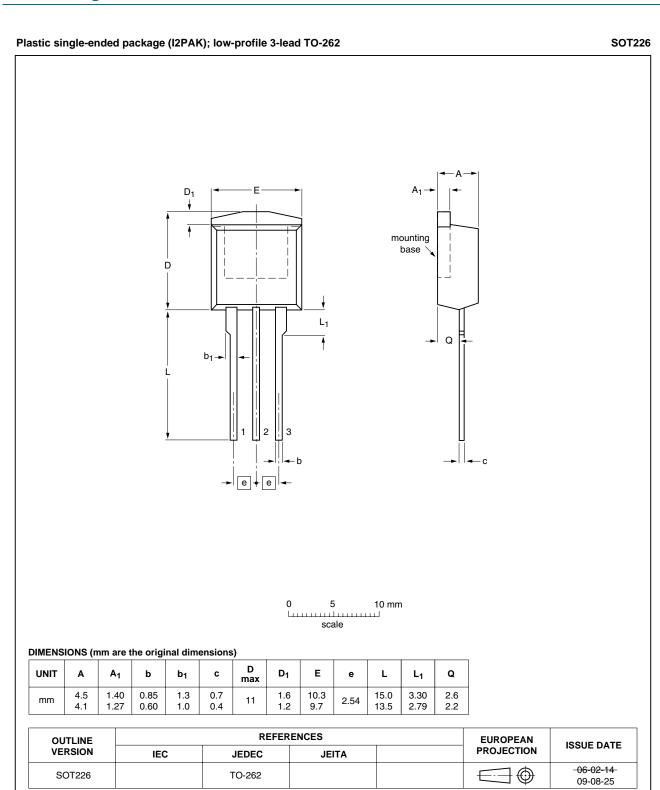


Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R5-40ES v.1	20110419	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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